DOCUMENT CHANGE REQUEST

DCR number 338

Changes required for: Qualification

Originator: aissa Nehdi

Date: 2007/06/19

Date sent: 2007/06/19

Organisation: CNES

Status: IMPLEMENTED

Title:	Transistors Low Power PNP, based on type 2N2907A		
Number:	5202/001	Issue:	2

Other documents affected:

Page:

2.4.1 Room Temperature Electrical Measurements
PAGE 11

Paragraph:

2.4.1 Room Temperature Electrical Measurements
PAGE 11

Original wording:

Proposed wording:

Forward-Current Transfer Ratio
Test Conditions : hFE1 VCE=-10V ; IC =-100µA instead of 100mA as written today

Justification:

Typing error during Issue 2/ release new ESCC format

Attachments:

N/A

Modifications:

N/A

Approval signature:

Date signed:

2007-06-19